



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



企业QQ二维码

## Product Summary

BV <sub>bss</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	2.4Ω @ V <sub>GS</sub> = 10V	510mA
	4.0Ω @ V <sub>GS</sub> = 4V	390mA

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

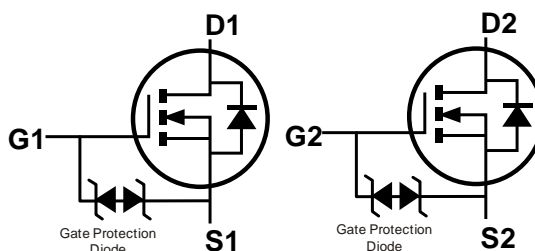
- DC-DC Converters
- Power Management Functions
- Analog Switch

## Mechanical Data

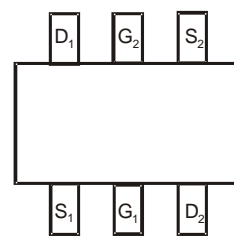
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.015 grams (Approximate)



SOT26  
Top View



Equivalent Circuit  
Per Element



Top View

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) (V <sub>GS</sub> = 10V)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	510 400	mA
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	580 470	mA
Continuous Drain Current (Note 6) (V <sub>GS</sub> = 4V)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	390 300	mA
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	440 340	mA
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	850	mA
Maximum Body Diode Continuous Current			I <sub>S</sub>	510	mA

### Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R <sub>θJA</sub>	157	°C/W
	t < 10s			121	
Total Power Dissipation (Note 6)			P <sub>D</sub>	0.98	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R <sub>θJA</sub>	113	°C/W
	t < 10s			88	
Thermal Resistance, Junction to Case (Note 6)			R <sub>θJC</sub>	26	
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.6	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.2	2.4	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 200mA
		—	1.5	4.0		V <sub>GS</sub> = 4V, I <sub>D</sub> = 200mA
Forward Transfer Admittance	Y <sub>fs</sub>	100	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 200mA
Diode Forward Voltage	V <sub>SD</sub>	0.5	0.8	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	30	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	3	5	pF	
Gate Resistance	R <sub>g</sub>	—	133	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	304	—	pC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	84	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	203	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.9	—	ns	V <sub>DS</sub> = 30V, I <sub>D</sub> = 0.2A, V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω, R <sub>L</sub> = 150Ω
Turn-On Rise Time	t <sub>r</sub>	—	3.4	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	15.7	—		
Turn-Off Fall Time	t <sub>f</sub>	—	9.9	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
 8. Guaranteed by design. Not subject to production testing.

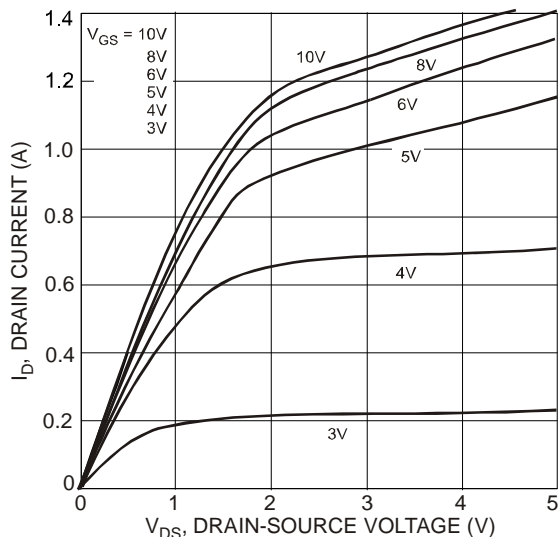


Fig. 1 Typical Output Characteristics

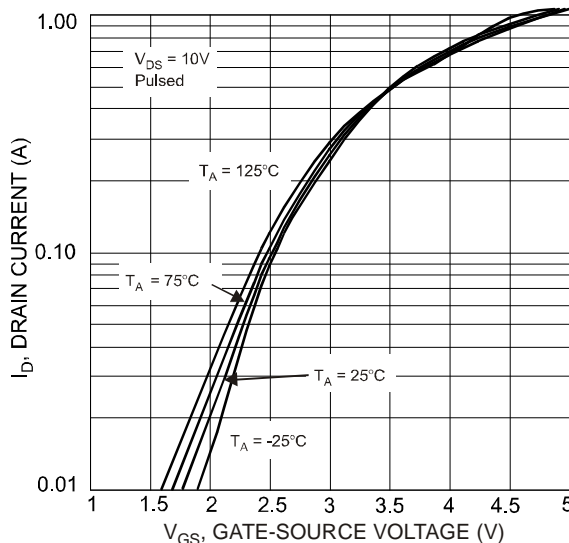


Fig. 2 Typical Transfer Characteristics

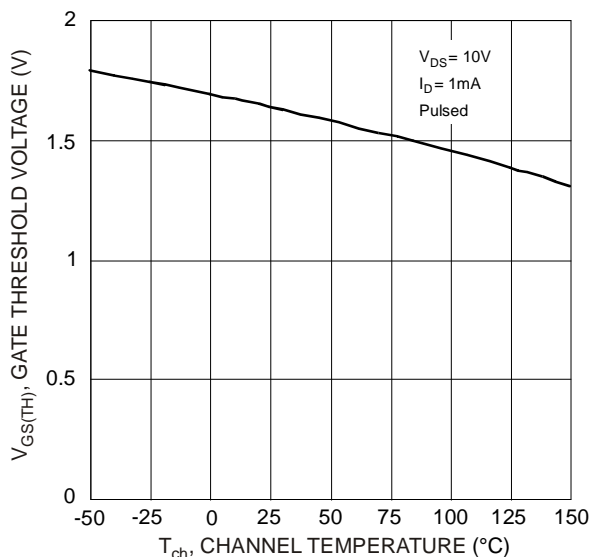


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

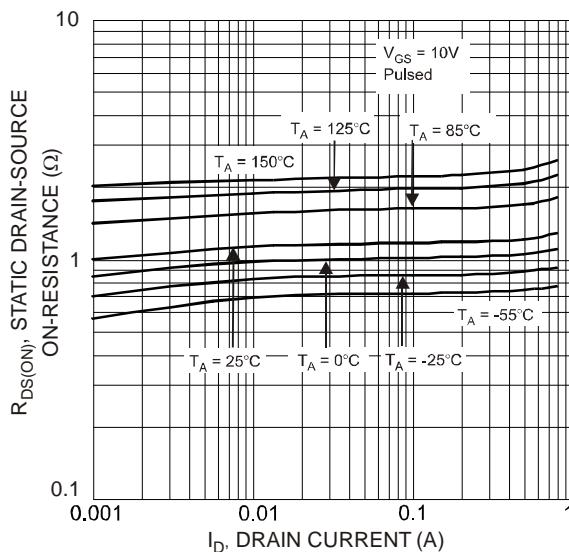


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

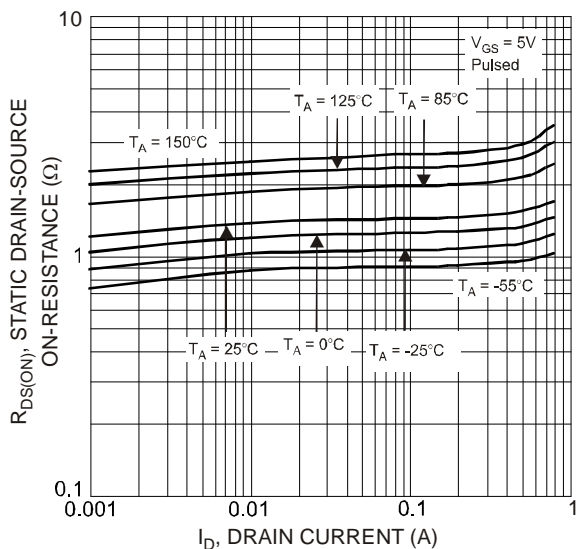


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

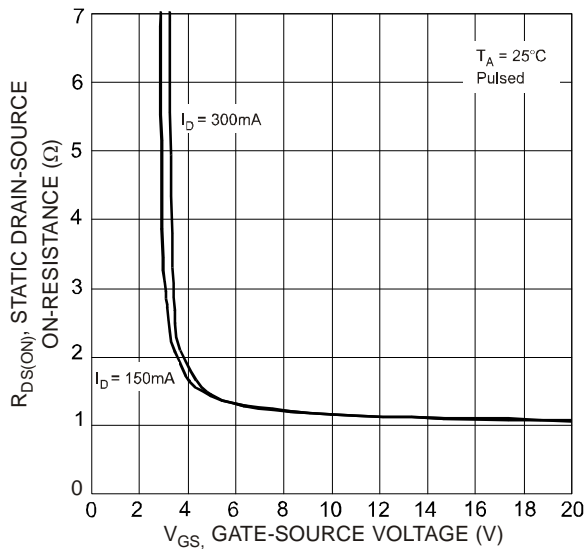


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

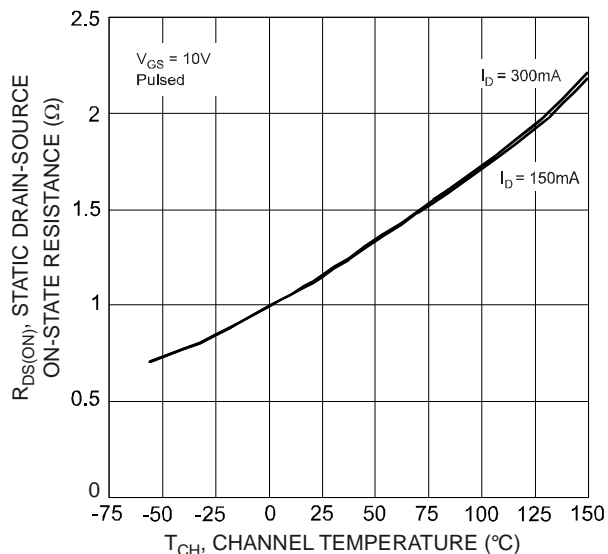


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

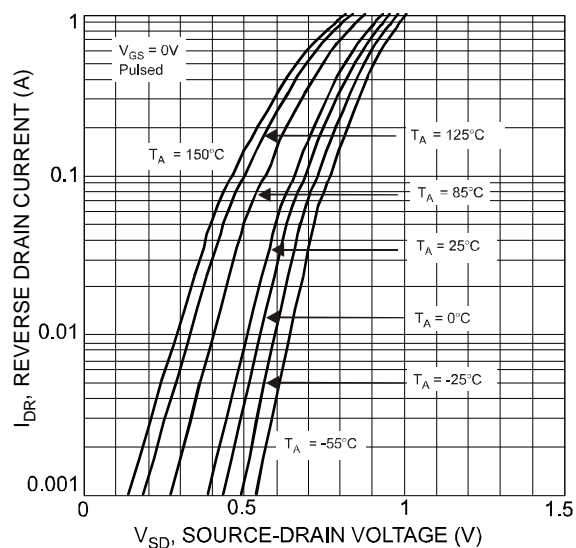


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

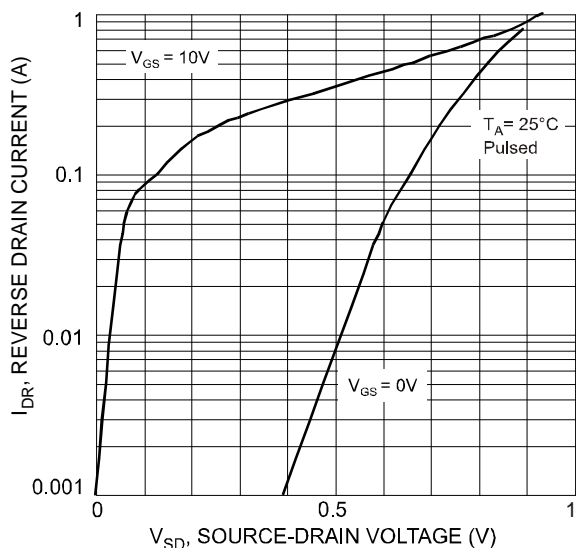


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

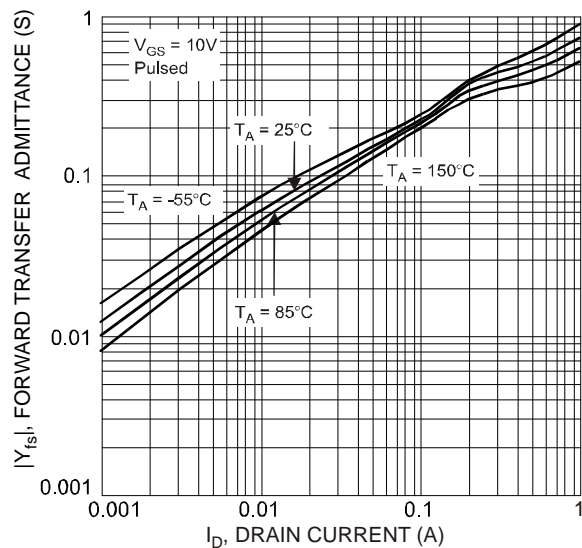
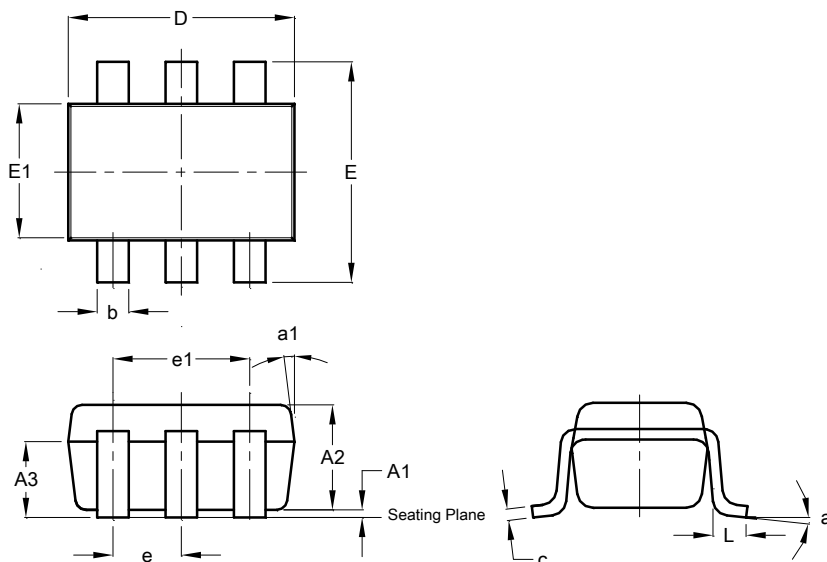


Fig.10 Forward Transfer Admittance vs. Drain Current

## Package Outline Dimensions

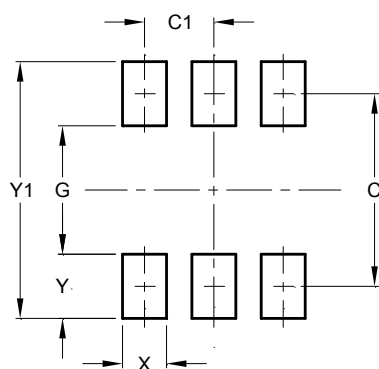
SOT26



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

## Suggested Pad Layout

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20